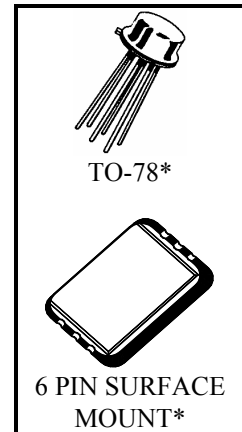


PNP DUAL SILICON TRANSISTOR
Qualified per MIL-PRF-19500/496
Devices
2N5795
**2N5796
2N5796U**
Qualified Level
**JAN
JANTX
JANTXV**
MAXIMUM RATINGS

Ratings	Symbol	Value		Units
Collector-Emitter Voltage	V_{CEO}	60		Vdc
Collector-Base Voltage	V_{CBO}	60		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current	I_C	600		mAdc
		One⁽¹⁾ Section	Both⁽²⁾ Sections	
Total Power Dissipation @ $T_A = +25^{\circ}\text{C}$	P_T	0.5	0.6	W
Operating & Storage Junction Temperature Range	T_J, T_{stg}	-65 to +175		$^{\circ}\text{C}$

 1) Derate linearly 2.86 mW/ $^{\circ}\text{C}$ for $T_A \geq +25^{\circ}\text{C}$

 2) Derate linearly 3.43 mW/ $^{\circ}\text{C}$ for $T_A \geq +25^{\circ}\text{C}$


*See MILPRF19500/496 for package outline

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}\text{C}$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage $I_C = 10 \text{ mAdc}$	$V_{(BR)CEO}$	60		Vdc
Collector-Base Cutoff Current $V_{CB} = 50 \text{ Vdc}$ $V_{CBO} = 60 \text{ Vdc}$	I_{CBO}		10 10	ηAdc μAdc
Emitter-Base Cutoff Current $V_{EB} = 3.0 \text{ Vdc}$ $V_{EB} = 5.0 \text{ Vdc}$	I_{EBO}		100 10	ηAdc μAdc

2N5795, 2N5796 JAN SERIES

ELECTRICAL CHARACTERISTICS (con't)

Characteristics	Symbol	Min.	Max.	Unit
ON CHARACTERISTICS (1)				
Forward-Current Transfer Ratio I _C = 100 μA _{dc} , V _{CE} = 10 V _{dc} I _C = 1.0 mA _{dc} , V _{CE} = 10 V _{dc} I _C = 10 mA _{dc} , V _{CE} = 10 V _{dc} I _C = 150 mA _{dc} , V _{CE} = 10 V _{dc} I _C = 300 mA _{dc} , V _{CE} = 10 V _{dc} I _C = 150 mA _{dc} , V _{CE} = 1.0 V _{dc}	2N5795	40 40 40 40 20 20	150	
I _C = 100 μA _{dc} , V _{CE} = 10 V _{dc} I _C = 1.0 mA _{dc} , V _{CE} = 10 V _{dc} I _C = 10 mA _{dc} , V _{CE} = 10 V _{dc} I _C = 150 mA _{dc} , V _{CE} = 10 V _{dc} I _C = 300 mA _{dc} , V _{CE} = 10 V _{dc} I _C = 150 mA _{dc} , V _{CE} = 1.0 V _{dc}	2N5796 2N5796U	75 100 100 100 50 50	300	
Collector-Emitter Saturation Voltage I _C = 150 mA _{dc} , I _B = 15 mA _{dc} I _C = 500 mA _{dc} , I _B = 50 mA _{dc}	V _{CE(sat)}		0.4 1.6	V _{dc}
Base-Emitter Saturation Voltage I _C = 150 mA _{dc} , I _B = 15 mA _{dc} I _C = 500 mA _{dc} , I _B = 50 mA _{dc}	V _{BE(sat)}		1.3 2.6	V _{dc}

DYNAMIC CHARACTERISTICS

Magnitude of Small-Signal Forward Current Transfer Ratio I _C = 20 mA _{dc} , V _{CE} = 20 V _{dc} , f = 100 MHz	h _{fe}	2.0	10	
Output Capacitance V _{CB} = 10 V _{dc} , I _E = 0, 100 kHz ≤ f ≤ 1.0 MHz	C _{obo}		8.0	pF
Input Capacitance V _{EB} = 2.0 V _{dc} , I _C = 0, 100 kHz ≤ f ≤ 1.0 MHz	C _{ibo}		25	pF

SWITCHING CHARACTERISTICS

Turn-On Time V _{CC} = 30 V _{dc} ; I _C = 150 mA _{dc} ; I _{B1} = 15 mA _{dc}	t _{on}		50	ns
Turn-Off Time V _{CC} = 30 V _{dc} ; I _C = 150 mA _{dc} ; I _{B1} = I _{B2} = 15 mA _{dc}	t _{off}		140	ns

1) Pulse Test: Pulse Width = 300μs, Duty Cycle ≤ 2.0%.